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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICATION OF:

Wolfgang Clemens et al.

SERIAL NO:

10/523,487

GROUP ART UNIT:

Not assigned

FILED:

February 4, 2005

EXAMINER:

Not assigned

CUSTOMER NO.:

27162

FOR:

Electronic Device

ATTY/DKT NO.:

415000-124

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria VA 22313-1450

SIR:

Pursuant to 37 C.F.R. §1.56(a), Applicant(s) hereby cite(s) the enclosed documents listed on the attached copy of Form PTO-1449 which are believed to be material to the patentability of the above-identified application.

This Information Disclosure Statement is filed in accordance with the paragraph of 37 CFR §1.97 indicated below:

<u>X</u> §1.97(b)	Inisi	nformation Disclosure Statement is filed:
	(1)	Within three months of the filing date of a national application; OR
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	ied in	ation Disclosure Statement is filed after the period paragraph (b) above, but before the mailing date of
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This Information Disclosure Statement provides a detailed list of the references cited in various pending applications listed in applicant's Disclosure Statement filed herewith.

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FIRST CLASS CERTIFICATE

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Respectfully submitted, Wolfgang Clemens et al.

William Squire Reg. No, ∕ 25,378

CARELLA, BYRNE BAIN, GILFILLAN, CECCHI, STEWART & OLSTEIN

5 Becker Farm Road Roseland, NJ 07068

Tel: (973)994-1700 Fax: (973)994-1744 Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it displays a valid OMB control number

for form 1449A/PTO Complete if Known 10/523,487 **Application Number** NFORMATION DISCLOSURE February 4, 2005 Filing Date STATEMENT BY APPLICANT First Named Inventor Wolfgang Clemens Not assigned **Group Art Unit** (Use as many sheets as necessary) **Examiner Name** Not assigned 7 Attorney Docket Number 411000-124 Of

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Examiner Signature	Date Considered	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED #256162

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Electronic Device

ATTY/DKT NO.:

411000-124

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

DISCLOSURE STATEMENT UNDER 37 CFR 1.56

SIR:

This paper is to bring to the attention of the PTO the following U.S. pending applications, all of which are related in different respects to organic electronic devices and/or method of making such devices such as transistors, diodes, integrated circuits and the like. Many of these applications also may have one or more common inventors.

Application No.	<u>Title</u>	Inventors	Atty. Dkt. No.
10/332,140	Method for the Production and Configuration of Organic Field-Effect Transistors (OFET)	Adolf Bernds et al.	411000-103
10/344,951	Organic Field-Effect Transistor (OFET), A Production Method Therefor, An Integrated Circuit Constructed From the Same and Their Uses	Adolf Bernds et al.	411000-99

Application No.	<u>Title</u>	Inventors	Atty. Dkt. No.
10/362,932	Organic Field Effect Transistor, Method for Structuring an OFET and Integrated Circuit	Adolf Bernds et al	411000-110
10/380,113	Organic Rectifier, Circuit, RFID Tag and Use of an Organic Rectifier	Adolf Bernds et al.	411000-106
10/380,206	Organic Memory, Identification Marker (RFID-TAG) with Organic Memory and Uses of an Organic Memory	Adolf Bernds et al.	411000-102
10/381,032	Electrode and/or Conductor Track for Organic Components and Production Method Thereof	Adolf Bernds et al.	411000-105
10/433,959	Organic Field Effect Transistor, Method For Structuring an OFET and Integrated Circuit	Adolf Bernds	411000-108
10/451,108	Organic Semiconductor, Production Method Therefor And The Use Thereof	Mark Giles et al.	411000.109
10/433,961	Device For Detecting and/or Transmitting at Least One Environmental Influence, Method for Producing Said Device and Use Thereof	Wolfgang Clemens et al.	411000-111
10/467,636	Organic Field Effect Transistor With a Photostructured Gate Dielectric, Method for the Production and Use Thereof in Organic Electronics	Adolf Bernds et al.	411000-104
10/473,050	Device With At Least Two Organic Electronic Components and Method for Producing the Same	Adolf Bernds et al.	411000-113
10/479,234	Organic Field Effect Transistor, Method for Production and Use Thereof in the Assembly of Integrated Circuits	Adolf Bernds et al.	411000-101
10/479,238	Method For Producing Conductive Structures by Means of Printing Technique, and Active Components Produced Therefrom For Integrated Circuits	Adolf Bernds et al.	411000-100
10/492,922	Insulator for An Organic Electronic Component	Erwann Guillet et al.	411000-115
10/492,923	Electronic Unit, Circuit Design for the Same and Production Method	Wolfgang Clemens et al.	411000-114
10/498,610	Organic Field Effect Transistor with Offset Threshold Voltage and the Use Thereof	Walter Fix et al.	411000-119

Application No.	<u>Title</u>	Inventors	Atty. Dkt. No.
10/508,640	Logic Component Comprising Organic Field Effect Transistors	Walter Fix et al.	411000-120
10/508,737	Device and Method for Laser Structuring Functional Polymers and the Uses Thereof	Adolf Bernds et al.	411000-121
10/517,750	Substrate for an Organic Field Effect Transistor, Use of the Substrate, Method of Increasing the Charge Carrier Mobility and Organic Field Effect Transistor (OFET)	Wolfgang Clemens et a.	411000-122
10/523,216	Electronic Component Comprising Predominantly Organic Functional Materials and a Process for the Production Thereof	Adolf Bernds et al.	411000-123
10/523,487	Electronic Device	Wolfgang Clemens et al.	411000-124
10/524,646	Organic Component For Overvoltage Protection And Associated Circuit	Walter Fix et al.	411000-127
Unknown	Organic Electronic Component With High-Resolution Structuring And Process For The Production Thereof	Wolfgang Clemens et al.	411000-128

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> May 11, 2005 ews Date

11, 2005 Fax: (973)994-1744

Respectfully submitted, Wolfgang Clemens et al.

CARELLA, BYRNE, BAIN, GILFILLAN,

CECCHI, STEWART & OLSTEIN

William Squire Reg. No 25,378

5 Becker Farm Road

Roseland, NJ 07068 Tel: (973)994-1700 U.S. Patent and Trademark Office; U.S. Department of Commerce

Substitute for form 1449A/PTO				Complete if Known		
				Application Number	10/523,487	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		RE	Filing Date	February 4, 2005		
		First Named Inventor	Wolfgang Clemens			
				Group Art Unit	Not assigned	
	(Use as many she	ets as necessary	<i>(</i>)	Examiner Name	Not assigned	
Sheet	1	Of	1	Attorney Docket Number	411000-124	

	T a::	T	U.S. PATENT DOCI		Dance Columns Lines M/L
Examiner Initial*	Cite No. ¹	Document Number Number-Kid Code ^{2 (if known)}	Publication- Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevan Figures Appear
	1	US-6,852,583	10/09/2003	Adolf Bernds et al.	See Disclosure Statement filed herewith
	2	US-10/344,951	N/A	Adolf Bernds et al.	
	3	US-10./362,932	10/02/2003	Adolf Bernds et al.	
	4	US-10/380,113	09/25/2003	Adolf Bernds et al.	
	5	US-10/380,206	N/A	Adolf Bernds et al.	
	6	US-10/381,032	N/A	Adolf Bernds et al.	
	7	US-10/433,959	N/A	Adolf Bernds	
	8	US-10/433,961	N/A	Wolfgang Clemens et al.	
	9	US-10/451,108	N/A	Mark Giles et al.	
	10	US-10/467,636	N/A	Adolf Bernds et al.	
	11	US-10/473,050	N/A	Adolf Bernds et al.	
	12	US-10/479,234	12/30/2004	Adolf Bemds et al.	
	13	US-10/479,238	N/A	Adolf Bernds et al.	
	14	US-10/492,922	N/A	Erwann Buillet et al.	
	15	US-10/492,923	12/23/2004	Wolfgang Clemens et al.	
	16	US-10/498,610	N/A	Walter Fix et al.	
	17	US-10/508,640	N/A	Walter Fix et al.	
	18	US-10/508,737	N/A	Adolf Bernds et al.	
	19	US-10/517,750	N/A	Wolfgang Clemens et al.	
	20	US-10/523,216	N/A	Adolf Bernds et al.	
·	21	US-10/523,487	N/A	Wolfgang Clemens et al.	
	22	US-10/524,646	N/A	Walter Fix et al.	
	23	Unknown	N/A	Wolfgang Clemens et al.	
Examiner Si	gnature	<u> </u>		Date Considered	

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. Applicant's unique citation designation number (optional). See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. MIPO Standard ST.16 if possible. Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.